

## CONTENTS

1. Ion Ranges and Energy Deposition in Insulators, 1  
By J.P. Biersack
  - 1.1 Repulsive Potentials and Nuclear Stopping  
in Ionic Insulators, 1
    - 1.1.1 Introduction, 1
    - 1.1.2 Evaluation of Interaction Potentials, 1
    - 1.1.3 Calculation of Scattering Angle and Transferred  
Energies in Atomic Collisions, 3
    - 1.1.4 Nuclear Stopping and Damage Production, 6
      - 1.1.4.1 Stopping by Binary Collisions, 6
      - 1.1.4.2 Stopping Enhancement in the Presence of  
Long Range Coulomb Forces, 7
      - 1.1.4.3 Energy Dissipation by Phonons, 9
      - 1.1.4.4 Damage Cross-Section, 10
    - 1.1.5 Results and discussion, 10
    - 1.1.6 Experimental Test on the Enhanced Stopping Effect  
in Ionic Crystals, 13
    - 1.1.7 Electronic Stopping in Insulators, 14
    - 1.1.8 Conclusions, 17
  - 1.2 Analytic Range Theories, 18
    - 1.2.1 Introduction, 18
    - 1.2.2 Directional Spread of Ion Motion During the  
Slowing-Down Process, 18
    - 1.2.3 Connection Between Angular Spread Parameter  
 $\tau$  and Energy Loss, 20
    - 1.2.4 Calculation of the Mean Projected Range, 21
    - 1.2.5 Heavy-Ion Ranges as an Example of Possible  
Analytic Treatment, 21
    - 1.2.6 Differential Equations and Universal Algorithm  
for Projected Ranges, 22
    - 1.2.7 Higher Terms and Precision, 24

- 1.2.8 Projected Ranges in Compound Materials, 25
  - 1.3 Monte-Carlo Range Calculations, 26
    - 1.3.1 Introduction, 26
    - 1.3.2 Physical Assumptions Used in the TRIM Code, 27
    - 1.3.3 Atomic Collisions, 28
    - 1.3.4 Simple Estimate on Energy Deposition, 29
    - 1.3.5 Free-Flight Path and Impact Parameter Selection, 30
    - 1.3.6 Electronic Energy Loss, 31
    - 1.3.7 Layered Target Structures, Surfaces, 32
    - 1.3.8 Selection of Target Atoms in Multi-Atomic Materials, 32
    - 1.3.9 Results and Discussion, 33
    - 1.3.10 Sputtering, 39
    - 1.3.11 Radiation Effects, 47
  - 1.4 Ion Range and Damage Distributions, 48
    - 1.4.1 Introduction, 48
    - 1.4.2 Range Calculations, 48
    - 1.4.3 Light Ion Implantation, 49
    - 1.4.4 Heavy Ion Range and Damage Profiles, 51
    - 1.4.5 Suitable Analytic Distribution Functions, 53
- References, 55
- 
- 2. The Sputtering of Insulators, 57
    - By R. Kelly
    - 2.1 Introduction, 57
      - 2.1.1 General Comments on Insulator Sputtering, 57
      - 2.1.2 Notation, 63
    - 2.2 Theory of Collisional Sputtering, 64
      - 2.2.1 General Comments on Sputtering Mechanisms, 64
      - 2.2.2 Prompt Collisional Sputtering, 64
      - 2.2.3 Slow Collisional Sputtering (Standard Theory), 68
      - 2.2.4 Slow Collisional Sputtering (Extended Theory), 70
      - 2.2.5 Sputtering of Molecules, 74

- 2.3 The Surface Binding Energy, 79
    - 2.3.1 Chemically Driven Effects in Sputtering, 79
    - 2.3.2 The Surface Binding Energy of a Metal or Alloy, 83
    - 2.3.3 The Surface Binding Energy of an Oxide or Halide, 87
  - 2.4 Results: a Comparison of Metal and Oxide Sputtering, 93
    - 2.4.1 General Comments, 93
    - 2.4.2 Total Yields, 93
    - 2.4.3 Atom Yields, 98
    - 2.4.4 Diatomic Yields, 101
    - 2.4.5 Ions and Excited States, 102
    - 2.4.6 Preferential Effects: General Comments, 103
    - 2.4.7 Preferential Effects: the Role of Binding Energies, 106
  - 2.5 Conclusions, 109
  - References, 110
- 3. Characterization Techniques for Ion Bombarded Insulators, 114**  
By J.A. Borders
- 3.1 Introduction, 114
  - 3.2 Analytical Requirements and Techniques for the Analysis of Ion Bombarded Insulators, 115
  - 3.3 Optical Methods, 117
    - 3.3.1 Infrared Spectroscopy, 118
    - 3.3.2 Optical and Ultra-Violet (UV) Spectroscopy, 121
    - 3.3.3 Fluorescence or Luminescence, 123
    - 3.3.4 Raman Spectroscopy, 125
  - 3.4 Structural Methods, 127
    - 3.4.1 Scanning Electron Microscopy, 127
    - 3.4.2 Transmission Electron Microscopy, 130
    - 3.4.3 X-Ray Diffraction, 134
  - 3.5 Energetic Ion Analysis Techniques, 135
    - 3.5.1 Rutherford Backscattering Spectrometry, 135

- 3.5.2 Elastic Recoil Detection, 139
- 3.5.3 Nuclear Reaction Analysis, 140
- 3.6 Surface Techniques, 144
  - 3.6.1 Auger and X-Ray Photoelectron Spectroscopies, 144
  - 3.6.2 SIMS and Ion Scattering Spectroscopy, 146
- 3.7 Other Techniques, 149
  - 3.7.1 Mössbauer Spectroscopy, 149
  - 3.7.2 Electron Paramagnetic Resonance, 151
- 3.8 Summary and Acknowledgements, 153
- References, 153
  
- 4. Defect Creation in Ion Bombarded Inorganic Insulators, 156
  - By A. Perez and P. Thevenard
  - 4.1 Brief Review on Point Defects and Extended Defects in Alkali Halides and Simple Oxides, 157
    - 4.1.1 Defects in Alkali Halide Crystals, 157
    - 4.1.2 Defects in Simple Oxides (MgO, TiO<sub>2</sub>), 159
  - 4.2 Intrinsic Defect Creation by Electronic Processes in Alkali Halides, 162
    - 4.2.1 Inhomogeneous Radial Distribution of Defects around the Particle Trajectory: Track Effects, 162
      - 4.2.1.1 Primary Energy Deposition, 162
      - 4.2.1.2 Secondary Energy Deposition, 164
    - 4.2.2 Experimental Studies of the Track Effect, 166
    - 4.2.3 Saturation Effect in the Track, 170
    - 4.2.4 Aggregation Mechanisms of Defects in the Tracks, 173
    - 4.2.5 Annealing Behaviour and Precipitation Processes, 176
  - 4.3 Intrinsic Defect Creation by Nuclear Collision Processes in Oxides (MgO, TiO<sub>2</sub>), 180
    - 4.3.1 Correlation Between Defect Profiles and Nuclear Energy Loss Profiles, 180

- 4.3.2 Extended Defect Formation in Highly Damaged Oxides, 182
- 4.4 Chemical Defects and Extrinsic Phase Precipitations Induced in Heavily Implanted Insulators, 184
  - 4.4.1 Chemical Bond Formation Between Implanted Atoms and Matrix Elements, 185
  - 4.4.2 New Compound Formation by Ion Implantation at High Dose, 186
- 4.5 Conclusion, 191
- References, 193
  
- 5. Ion Beam Modification of Glasses, 195
  - By G.W. Arnold and P. Mazzoldi
  - 5.1 Introduction, 195
  - 5.2 Glass Structure, 195
  - 5.3 Implantation-induced defects, 198
  - 5.4 Volume Changes, 200
    - 5.4.1 Refractive Index Changes, 201
    - 5.4.2 Surface Stress Measurements, 203
    - 5.4.3 Hardness, 204
    - 5.4.4 Chemical Durability, 206
  - 5.5 Optical Properties, 207
    - 5.5.1 Optical Absorption, 207
    - 5.5.2 Luminescence, 209
  - 5.6 Compositional Changes, 211
    - 5.6.1 Alkali Depletion, 211
    - 5.6.2 Nucleation and Crystallization, 217
  - 5.7 Concluding Remarks, 219
  - References, 220
  
- 6. The Mechanical and Tribological Properties of Ion Implanted Ceramics, 223
  - By C.J. McHargue
  - 6.1 Introduction, 223

- 6.2 Microstructure of Implanted Ceramics, 223
- 6.3 Hardness, 227
- 6.4 Fracture Toughness, 233
- 6.5 Transverse Rupture Strength, 236
- 6.6 Implantation-Induced Residual Stresses, 237
- 6.7 Tribological Properties, 239
- 6.8 Summary, 242
- 6.9 Acknowledgement, 243
- References, 243
  
- 7. **Synthesis of Dielectric Layers in Silicon by Ion  
Implantation, 245**  
By I.H. Wilson
  - 7.1 Preamble, 245
    - 7.1.1 Past, Present and Future, 245
    - 7.1.2 Acknowledgements, 247
  - 7.2 Chemistry, 247
    - 7.2.1 Energetics, 248
    - 7.2.2 Bonds, 249
    - 7.2.3 Location of the Lattice Position of Implanted  
Impurities, 252
    - 7.2.4 Formation of a Second Phase, 252
    - 7.2.5 Experimental Determination of the Chemical State  
of Implanted Atoms, 253
  - 7.3 Defects, 259
    - 7.3.1 Intrinsic Defects, 260
    - 7.3.2 Radiation Damage: Point Defects and Defect  
Complexes, 262
    - 7.3.3 Radiation Damage: the Crystalline-Amorphous  
Transition, 267
    - 7.3.4 Dislocations and Stacking Faults, 268
  - 7.4 Mass Transport, 269
    - 7.4.1 Driving Forces, 269
    - 7.4.2 Chemical Segregation, 271

|       |   |     |
|-------|---|-----|
| 7.4.3 | Stress and Other Effects,                                     | 274 |
| 7.4.4 | Experiments on Mass Transport,                                | 274 |
| 7.4.5 | Models of Mass Transport,                                     | 278 |
| 7.4.6 | Diffusion Rates and Diffusion Mechanisms,                     | 279 |
| 7.5   | Precipitation,  | 280 |
| 7.5.1 | Oxide Precipitates,   | 280 |
| 7.5.2 | Nitride Precipitates,   | 286 |
| 7.6   | Microstructure,   | 288 |
| 7.6.1 | Oxygen Implantation: the As-Implanted State,                  | 288 |
| 7.6.2 | Oxygen Implantation: after Annealing (Beam Heated Specimens), | 290 |
| 7.6.3 | Nitrogen Implantation: As-Implanted,                          | 292 |
| 7.6.4 | Nitrogen Implantation: Annealed Structures,                   | 293 |
| 7.6.5 | Carbon Implantation,  | 295 |
|       | References,   | 297 |

## **8. Ion Beam Effects in Organic Molecular Solids and Polymers, 301**

By T. Venkatesan, L. Calcagno, B.S. Elman and G. Foti

|       |  |     |
|-------|--|-----|
| 8.1   | Introduction,  | 301 |
| 8.2   | Energy Loss, Range and Energy Deposition,                          | 303 |
| 8.3   | Molecular Emission,  | 309 |
| 8.4   | Polymer Stoichiometry,   | 313 |
| 8.5   | Ion Beam Induced Polymerization,                                   | 317 |
| 8.6   | Molecular Weight,  | 322 |
| 8.7   | Polymer Solubility,  | 325 |
| 8.8   | Electronic and Optical Properties of Ion Beam Irradiated Polymers, | 330 |
| 8.8.1 | Electronic Properties,   | 330 |
| 8.8.2 | Optical Properties,  | 350 |
| 8.9   | Structure of Ion Implanted Polymers,                               | 355 |
| 8.10  | Applications,  | 364 |
|       | References,  | 374 |

**9. Condensed Gases, 380**

By W.L. Brown

- 9.1 The Special Properties of Condensed Molecular and Rare Gas Solids, 380
- 9.2 Sputtering, 380
  - 9.2.1 Collisional Sputtering, 381
  - 9.2.2 Electronic Sputtering, 386
- 9.3 Decomposition and New Molecule Formation, 396
  - 9.3.1 Mass Spectroscopy of Species Ejected from Pure Condensed Molecular Gases, 397
  - 9.3.2 Mass Spectroscopy of New Species Produced in Condensed Gas Mixtures, 403
  - 9.3.3 Optical Spectroscopy of Pure and Mixed Condensed Gases, 403
  - 9.3.4 Composition Changes and Residues, 405
- 9.4 Luminescence, 407
- 9.5 Summary, 408
- References, 409

**10. Optoelectronic Materials, 412**

By G. Gotz

- 10.1 Introduction, 412
- 10.2 SiO<sub>2</sub> ( $\alpha$ -Quartz), 412
  - 10.2.1 Defect Generation, 413
  - 10.2.2 Optical Properties and Density, 416
  - 10.2.3 Defect Annealing and Transformation, 419
  - 10.2.4 Conclusion, 421
- 10.3 LiNbO<sub>3</sub>, 422
  - 10.3.1 Defect Generation, 423
  - 10.3.2 Volume Expansion, 427
  - 10.3.3 Optical Properties, 428
  - 10.3.4 Defect Annealing and Transformation, 432
  - 10.3.5 Conclusions, 439
- 10.4 Optical Waveguides, 441



10.5 Summary, 445

References, 446

## 11. Ferrimagnetic Garnets, 449

By P. Gerard

11.1 Introduction, 449

11.2 Garnet Material, 452

11.2.1 Crystalline Structure, 452

11.2.2 Magnetization, 453

11.2.3 Bubble Garnet Material, 454

11.3 Implantation Effects, 457

11.3.1 Implant and damage profiles, 458

11.3.2 Definition of dose levels, 460

11.3.3 Pure magnetostriction implantation effect, 462

11.4 Characterization, 464

11.4.1 Rutherford Backscattering (RBS)

and Channeling, 464

11.4.2 Kinematic X-ray Double Crystal Diffraction, 465

11.4.3 Ferromagnetic Resonance, 467

11.4.4 Conversion Electron Mössbauer Spectroscopy, 471

11.5 Neon Implantation, 473

11.5.1 Influence of Doses, 473

11.5.2 Annealing Treatments, 476

11.6 Hydrogen and Deuterium Implantations, 478

11.6.1 H<sup>+</sup> or D<sup>+</sup> Implantation Effect, 479

11.6.2 Annealing Treatments, 481

11.6.3 Microscopic Approach by CEMS, 487

11.7 High Dose Implantation, 488

11.7.1 Profile of Implantation Effects, 489

11.7.2 Epitaxial Regrowth Mechanism, 490

11.7.3 Specific Dopant Effect, 492

11.7.4 Ion Mixing in Garnets, 493

11.8 Conclusion, 495

References, 496

**12. Nuclear Waste Materials, 501**

By Hj. Matzke

- 12.1 Introduction, 501
- 12.2 The Nuclear Fuel Cycle and High Level Waste, 503
- 12.3 Waste Glasses and Ceramics used or suggested for Radwaste Solidification, 507
  - 12.3.1 Waste Glasses, 507
  - 12.3.2 Large Scale Production of Waste Glasses, 509
  - 12.3.3 Glass Ceramics and Ceramic Matrices, 509
- 12.4 Conditions for Safe Storage of Solidified HLW in Deep Geological Formations, 510
- 12.5 Application of Ion Beams to HLW Products, 513
  - 12.5.1 Use of Ion Beam Techniques for Leaching Studies, 513
  - 12.5.2 Use of Ion Beam Techniques to Study Radiation Effects, 519
- 12.6 Effects of  $\alpha$ -Decay of Incorporated Actinides in Waste Matrices, 521
- 12.7 Summary, 527
- References, 528

**13. Role of Defects on the Aqueous Dissolution of Ion-Bombarded Insulators, 531**

By G. Della Mea, J.-C. Dran and J.-C. Petit

- 13.1 Introduction, 531
- 13.2 Relationship Between Ion-Induced Defects and Etching Features, 532
  - 13.2.1 Ion-Induced Enhancement of the Dissolution Rate: Evidence for a Critical Irradiation Dose, 532
  - 13.2.2 Description of the Percolation Model, 535
  - 13.2.3 Tentative Structural Significance of the Critical Fluence, 537
  - 13.2.4 Energy and Atomic Number Dependence of the Dissolution Characteristics, 537

- 13.2.5 Inferred Defect Structure, 539
- 13.3 Ion Implantation Effects on the Hydration Features, 543
  - 13.3.1 Main Features of the Hydration of Ion Implanted Silica, 544
  - 13.3.2 Role of the Crystalline Structure on the Ion-Induced Hydration, 548
  - 13.3.3 Effect of Thermal Annealing on the Hydrogen Uptake, 549
  - 13.3.4 Influence of Atomic Number and Energy of Incident Ions on the Hydration Characteristics, 550
  - 13.3.5 Effect of Ion Implantation on the Hydration of Na-Containing Silicates, 551
- 13.4 Application to Earth Sciences, 554
  - 13.4.1 Use of Ion Implantation for Simulating an Internal  $\alpha$ -Irradiation, 554
  - 13.4.2 Radiation-Enhanced Release of Uranium from Minor Minerals in Rocks, 555
- 13.5 Conclusion, 556
- References, 557
  
- 14. Chemical Effects of Ion Bombardment, 558
  - By G.K. Wolf and K. Roessler
  - 14.1 Introduction, 558
    - 14.1.1 Content and Limitations, 558
    - 14.1.2 Experimental Methods, 559
  - 14.2 Principles and Mechanisms, 560
    - 14.2.1 Hot Atom Chemistry, 560
    - 14.2.2 Radiation Chemistry, 565
  - 14.3 Synthesis and Decomposition, 566
    - 14.3.1 Bombardment of Metals with non-Metals, 567
    - 14.3.2 Bombardment of Semiconductors with non-Metals, 569
    - 14.3.3 Ion Bombardment of Compounds, 570
  - 14.4 Applications, 570

- 14.4.1 Labelling, 570
- 14.4.2 Surface Chemistry, 571
  - 14.4.2.1 Catalytic Reactions, 572
  - 14.4.2.2 Corrosion Reactions, 574
  - 14.4.2.3 Formation of Amorphous Hydrogenated  
Carbon Films, 576
- 14.4.3 Desorption and Etching, 576
- 14.4.4 Cosmic Chemistry, 579
- References, 581

**15. Ion Beam Effects on Thin Film Adhesion, 585**

By J.E.E. Baglin

- 15.1 Introduction, 585
- 15.2 Origins of Adhesion, 586
  - 15.2.1 Thermodynamic Criteria, 586
  - 15.2.2 Van der Waals Forces, 587
  - 15.2.3 Electrostatic Attraction, 587
  - 15.2.4 Chemical Bonding; Metallic Bonding, 588
  - 15.2.5 Interface Structure; Bonding Networks, 588
  - 15.2.6 Intermediate Coupling Layers, 590
  - 15.2.7 Mechanical Effects, 591
- 15.3 Causes of Delamination or Reduced Adhesion, 592
  - 15.3.1 Residual Film Stress, 592
  - 15.3.2 Thermal Stress, 594
- 15.4 Adhesion Testing, 594
  - 15.4.1 Scotch Tape Test, 595
  - 15.4.2 Peel Test, 596
  - 15.4.3 Scratch Test, 598
  - 15.4.4 Q-Tip or Cotton Bud Test, 598
  - 15.4.5 Pin-Pull Test, 599
  - 15.4.6 "Sessile drop" Test, 600
- 15.5 Adhesion Enhancement, 601
  - 15.5.1 Irradiation at the Interface, 601
    - (i) Experimental Review, 602

|            |   |            |
|------------|---|------------|
| (ii)       | Basic Mechanisms,   | 610        |
| (iii)      | Ion-Interface Interaction,  | 611        |
| (iv)       | Contaminant Layers,   | 616        |
| (v)        | Interface Chemistry,  | 618        |
| (vi)       | Summary,  | 619        |
| 15.5.2     | Substrate Surface Activation,   | 620        |
| (i)        | Adatom Species,   | 620        |
| (ii)       | Ion Bombardment,  | 621        |
| (iii)      | Interface "Phase",  | 623        |
| 15.5.3     | Ion Assisted Deposition,  | 625        |
| 15.6       | Future Possibilities,   | 625        |
|            | References,   | 627        |
| <b>16.</b> | <b>Astrophysical Implications of Ions Incident<br/>on Insulators,</b> | <b>631</b> |
|            | By L.J. Lanzerotti and R.E. Johnson                                   |            |
| 16.1       | Introduction,   | 631        |
| 16.2       | The Moon and Mercury,   | 636        |
| 16.3       | Jupiter: the Satellite Io,  | 637        |
| 16.4       | Jupiter: Europa, Ganymede, and Callisto,                              | 637        |
| 16.5       | Saturn: the Rings and Satellites,                                     | 638        |
| 16.6       | Uranus, Neptune, Pluto,   | 639        |
| 16.7       | Comets and Other Icy Bodies,  | 640        |
| 16.8       | Interplanetary Grains,  | 641        |
| 16.9       | Summary,  | 642        |
| 16.10      | Acknowledgements,   | 642        |
|            | References,   | 642        |
|            | Subject Index,  | 645        |
|            | <b>Appendix: Tables of Ion Ranges in Insulators</b>                   |            |
|            | Introduction,   | A1         |
|            | Index 1: Targets,   | A2         |
|            | Index 2: Targets in Alphabetical Order,                               | A3         |
|            | Matrix of Ion-Target Combination,                                     | A4         |
|            | Tables,   | A4-A93     |